C.F.

Notice of Allowability	Application No.	Applicant(s)
	09/831,763	MEYER ET AL.
	Examiner	Art Unit
	Brian L. Mutschler	1753
The MAILING DATE of this communication app All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85 NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT F of the Office or upon petition by the applicant. See 37 CFR 1.31	S (OR REMAINS) CLOSED in i) or other appropriate commi RIGHTS. This application is s	n this application. If not included
1. This communication is responsive to Response filed 12 M	<u>lay 2004</u> .	
2. The allowed claim(s) is/are <u>1-9</u> .		
3. May The drawings filed on 11 May 2001 are accepted by the E	xaminer.	
<ul> <li>4.  Acknowledgment is made of a claim for foreign priority unall All b)  Some* c)  None of the:</li> <li>1.  Certified copies of the priority documents have 2.  Certified copies of the priority documents have 3.  Copies of the certified copies of the priority documents have a copies of the priority documents have a certified copies of the certified copies of the priority documents have a certified copies of the cer</li></ul>	e been received e been received in Applicatio	n No
International Bureau (PCT Rule 17.2(a)).  * Certified copies not received:	cuments have been received	and this riadional stage application from the
Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONN THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.	of this communication to file MENT of this application.	a reply complying with the requirements
5. A SUBSTITUTE OATH OR DECLARATION must be subm INFORMAL PATENT APPLICATION (PTO-152) which giv	nitted. Note the attached EXA es reason(s) why the oath or	MINER'S AMENDMENT or NOTICE OF declaration is deficient.
<ul> <li>6. ☐ CORRECTED DRAWINGS ( as "replacement sheets") must (a) ☐ including changes required by the Notice of Draftspers</li> <li>1) ☐ hereto or 2) ☐ to Paper No./Mail Date</li> <li>(b) ☐ including changes required by the attached Examiner' Paper No./Mail Date</li> </ul>	son's Patent Drawing Review	
Identifying indicia such as the application number (see 37 CFR 1 each sheet. Replacement sheet(s) should be labeled as such in t	.84(c)) should be written on th	e drawings in the front (not the back) of
<ol> <li>DEPOSIT OF and/or INFORMATION about the depo attached Examiner's comment regarding REQUIREMENT</li> </ol>	sit of BIOLOGICAL MATE	RIAL must be submitted. Note the
Attachment(s) 1. ☑ Notice of References Cited (PTO-892)	5. Notice of Inf	ormal Patent Application (PTO-152)
2. Notice of Draftperson's Patent Drawing Review (PTO-948)	6. 🗌 Interview Su	mmary (PTO-413),
3. Information Disclosure Statements (PTO-1449 or PTO/SB/C	08), 7. ☐ Examiner's /	Mail Date Amendment/Comment
<ol> <li>Examiner's Comment Regarding Requirement for Deposit of Biological Material</li> </ol>	8. ⊠ Examiner's 9. □ Other	Statement of Reasons for Allowance
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## **DETAILED ACTION**

## Allowable Subject Matter

1. The following is an examiner's statement of reasons for allowance:

The instant claims are distinguished over the prior art of record by providing a method for electrolytically depositing copper layers on a semiconductor substrate using a bath containing Fe(II) or Fe(III) compounds. Although DE 195 45 231 A1 discloses a method for electrolytically plating copper on circuit boards using iron compounds to replenish the electrolyte, at the time of the invention, iron was considered detrimental to plating on semiconductors. In U.S. Pat. No. 6,596,148, Belongia et al. teach, "lons such as iron have a deleterious effect on performance of the plating process" (col. 4, lines 50-52). Choi et al. teach that iron contamination affects leakage current and carrier lifetime in semiconductors (see Choi et al., "Latent Iron in Silicon," Jpn. J. Appl. Phys., Vol. 40 (2001), pp. L915-L917). Istratov et al. further teach of the detrimental effects iron has on semiconductor materials (see Istratov et al., "Iron and its complexes in silicon," Appl. Phys. A 69 (1999), pp. 13-44 and Istratov et al., "Iron contamination in silicon technology," Appl. Phys. A 70 (2000), pp. 489-534). Based on the knowledge of one skilled in the art at the time the instant invention was made, it would not have been obvious to use the iron-containing plating bath of DE '231 for plating semiconductors because iron was considered deleterious to the plating process, and one skilled in the art would not have had a reasonable expectation of success or motivation to use such a plating bath.

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Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

2. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Brian L. Mutschler whose telephone number is (571) 272-1341. The examiner can normally be reached on Monday-Friday from 7:30am to 4:00pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nam Nguyen can be reached on (571) 272-1342. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

BLM May 27, 2004 NAM NGUYEN
SUPERVISORY PATENT EXAMINER
TECHNOLOGY CENTER 1700